



Features and Benefits Low On-Resistance Low Input Capacitance Fast Switching Speed Low Input/Output Leakage

be found at

products/.

AEC-Q) for High Reliability.

Datasheet (DMN4035LQ)

Mechanical Data

Case: SOT23

N-CHANNEL ENHANCEMENT MODE MOSFET

Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2) Halogen and Antimony Free. "Green" Device (Note 3) For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can

https://www.diodes.com/products/automotive/automotive-

This part is qualified to JEDEC standards (as references in

An Automotive-Compliant Part is Available Under Separate

Case Material: Molded Plastic, "Green" Molding Compound.

Terminals: Finish — Matte Tin Annealed over Copper Leadframe.

https://www.diodes.com/quality/product-definitions/

UL Flammability Classification Rating 94V-0

Moisture Sensitivity: Level 1 per J-STD-020

Solderable per MIL-STD-202, Method 208 3

Terminals Connections: See Diagram Below

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max
	42mΩ @ V _{GS} = 10V	4.6A
40V	52mΩ @ V _{GS} = 4.5V	4.1A

Description and Applications

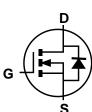
This MOSFET is designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

SOT23



Top View



Weight: 0.008 grams (Approximate) D G Top View

Pin-Out

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN4035L-7	SOT23	3000/Tape & Reel
DMN4035L-13	SOT23	10000/Tape & Reel

Internal Schematic

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:

Date Code Ke	v		35L	. ¥]	Y Y	M = Date 0 or $\overline{Y} = Yea$	ict Type Ma Code Markir ar (ex: G = 2 ex: 9 = Sep	ng 2019)		
Year	2019	20	20	2021	2022	20	23	2024	2025	20	26
Code	G		-		J		<	L	М	1	N
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov
Code	1	2	3	4	5	6	7	8	9	0	N

2027 0 Dec

D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	Vdss	40	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 6) $V_{GS} = 10V$ Steady $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$			lo	4.6 3.7	А
Maximum Body Diode Forward Current (Note 6)		ls	1.5	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	ldм	25	A		
Pulsed Source Current (10µs Pulse, Duty Cycle = 1	lsм	25	A		

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Power Dissipation (Note 5)		PD	0.72	W
Thermal Resistance, Junction to Ambient (Note 5)	Reja	171	°C/W	
Power Dissipation (Note 6)		PD	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	93	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

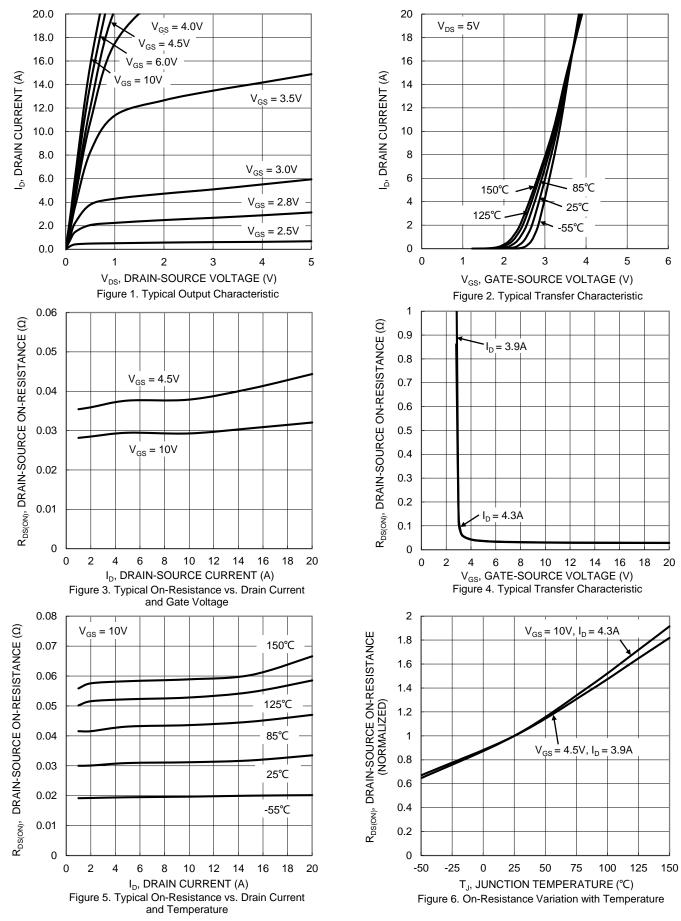
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_		V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	$V_{DS} = 40V, V_{GS} = 0V$	
Gate-Source Leakage	lgss	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)			•	•	•	·	
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Descent	_	30	42	mΩ	Vgs = 10V, ID = 4.3A	
Static Drain-Source On-Resistance	RDS(ON)	_	40	52	11152	VGS = 4.5V, ID = 3.9A	
Diode Forward Voltage	V _{SD}	-	0.7	1.1	V	V _{GS} = 0V, I _S = 1.25A	
DYNAMIC CHARACTERISTICS (Note 8)						-	
Input Capacitance	Ciss	_	574	_			
Output Capacitance	Coss	_	87.8	_	pF	$V_{DS} = 20V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	38.7	_			
Gate Resistance	Rg	_	1.6		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	5.9				
Total Gate Charge (V _{GS} = 10V)	Qg	-	12.5		nC		
Gate-Source Charge	Q _{gs}	-	1.7		nc	$V_{DS} = 20V, I_D = 3.9A$	
Gate-Drain Charge	Q _{gd}		2.2				
Turn-On Delay Time	tD(ON)		3.1				
Turn-On Rise Time	t _R		2.6	_		$\label{eq:VDD} \begin{split} V_{DD} &= 20 V, V_{GS} = 10 V, \\ R_L &= 20 \Omega, R_G = 6 \Omega \end{split}$	
Turn-Off Delay Time	t _{D(OFF)}		15	_	ns		
Turn-Off Fall Time	tF	_	5.5	_	1		
Reverse Recovery Time	t _{RR}	_	6.5		ns		
Reverse Recovery Charge	Q _{RR}	_	1.2		nC	nC IF = 3.9A, di/dt = 500A/µs	

Notes:

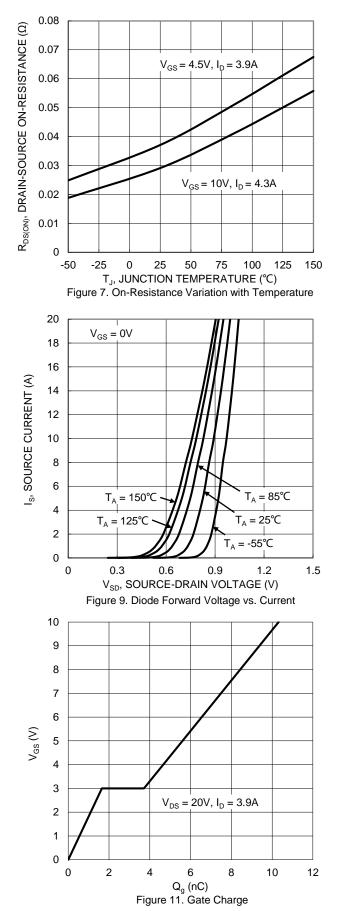
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

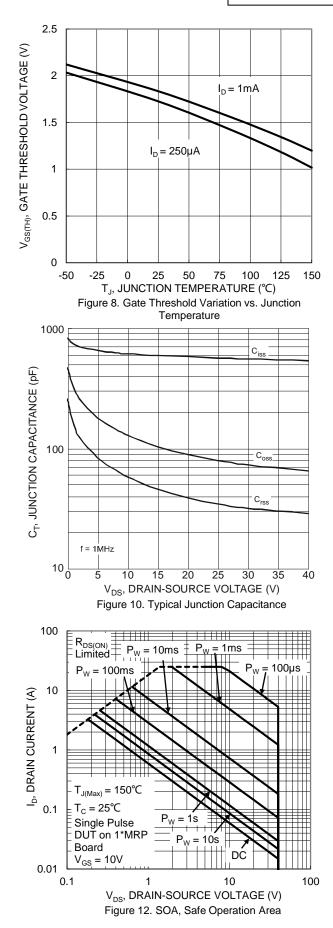




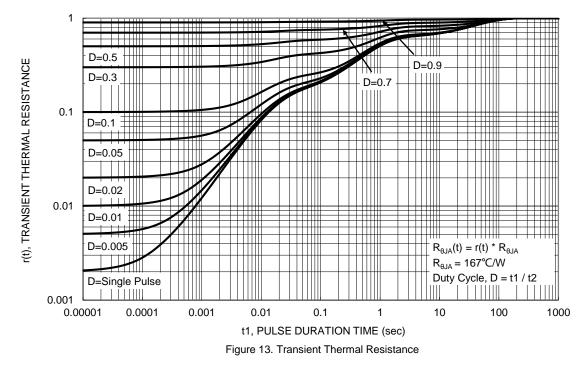








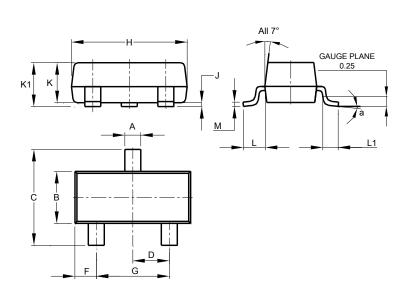






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



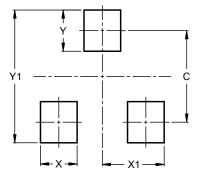
SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
ĸ	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
Μ	0.085	0.150	0.110				
а	0°	8°					
All	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

SOT23



Dimensions	Value (in mm)				
С	2.0				
Х	0.8				
X1	1.35				
Y	0.9				
Y1	2.9				



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